

IGBT-Wechselrichter / IGBT-inverter**Höchstzulässige Werte / maximum rated values**

Kollektor-Emitter-Sperrspannung collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{CES}	1200	V
Kollektor-Dauergleichstrom DC-collector current	$T_C = 80^{\circ}\text{C}$ $T_C = 25^{\circ}\text{C}$	$I_{C\text{ nom}}$ I_C	100 200	A A
Periodischer Kollektor Spitzenstrom repetitive peak collector current	$t_P = 1\text{ ms}$, $T_C = 80^{\circ}\text{C}$	I_{CRM}	200	A
Gesamt-Verlustleistung total power dissipation	$T_C = 25^{\circ}\text{C}$	P_{tot}	780	W
Gate-Emitter-Spitzenspannung gate-emitter peak voltage		V_{GES}	+/-20	V

Charakteristische Werte / characteristic values

			min.	typ.	max.	
Kollektor-Emitter Sättigungsspannung collector-emitter saturation voltage	$I_C = 100\text{ A}$, $V_{GE} = 15\text{ V}$, $T_{vj} = 25^{\circ}\text{C}$ $I_C = 100\text{ A}$, $V_{GE} = 15\text{ V}$, $T_{vj} = 125^{\circ}\text{C}$	$V_{CE\text{ sat}}$		2,10 2,40	2,60 2,90	V V
Gate-Schwellenspannung gate threshold voltage	$I_C = 4,00\text{ mA}$, $V_{CE} = V_{GE}$, $T_{vj} = 25^{\circ}\text{C}$	V_{GEth}	4,5	5,5	6,5	V
Gateladung gate charge	$V_{GE} = -15\text{ V} \dots +15\text{ V}$	Q_G		1,10		μC
Interner Gatewiderstand internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$	R_{Gint}		2,5		Ω
Eingangskapazität input capacitance	$f = 1\text{ MHz}$, $T_{vj} = 25^{\circ}\text{C}$, $V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$	C_{ies}		6,50		nF
Rückwirkungskapazität reverse transfer capacitance	$f = 1\text{ MHz}$, $T_{vj} = 25^{\circ}\text{C}$, $V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$	C_{res}		0,42		nF
Kollektor-Emitter Reststrom collector-emitter cut-off current	$V_{CE} = 1200\text{ V}$, $V_{GE} = 0\text{ V}$, $T_{vj} = 25^{\circ}\text{C}$	I_{CES}			5,0	mA
Gate-Emitter Reststrom gate-emitter leakage current	$V_{CE} = 0\text{ V}$, $V_{GE} = 20\text{ V}$, $T_{vj} = 25^{\circ}\text{C}$	I_{GES}			400	nA
Einschaltverzögerungszeit (ind. Last) turn-on delay time (inductive load)	$I_C = 100\text{ A}$, $V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 6,8\ \Omega$, $T_{vj} = 25^{\circ}\text{C}$ $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 6,8\ \Omega$, $T_{vj} = 125^{\circ}\text{C}$	$t_{d\text{ on}}$		0,06 0,06		μs μs
Anstiegszeit (induktive Last) rise time (inductive load)	$I_C = 100\text{ A}$, $V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 6,8\ \Omega$, $T_{vj} = 25^{\circ}\text{C}$ $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 6,8\ \Omega$, $T_{vj} = 125^{\circ}\text{C}$	t_r		0,05 0,05		μs μs
Abschaltverzögerungszeit (ind. Last) turn-off delay time (inductive load)	$I_C = 100\text{ A}$, $V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$, $R_{Goff} = 6,8\ \Omega$, $T_{vj} = 25^{\circ}\text{C}$ $V_{GE} = \pm 15\text{ V}$, $R_{Goff} = 6,8\ \Omega$, $T_{vj} = 125^{\circ}\text{C}$	$t_{d\text{ off}}$		0,35 0,40		μs μs
Fallzeit (induktive Last) fall time (inductive load)	$I_C = 100\text{ A}$, $V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$, $R_{Goff} = 6,8\ \Omega$, $T_{vj} = 25^{\circ}\text{C}$ $V_{GE} = \pm 15\text{ V}$, $R_{Goff} = 6,8\ \Omega$, $T_{vj} = 125^{\circ}\text{C}$	t_f		0,06 0,08		μs μs
Einschaltverlustenergie pro Puls turn-on energy loss per pulse	$I_C = 100\text{ A}$, $V_{CE} = 600\text{ V}$, $L_S = 60\text{ nH}$ $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 6,8\ \Omega$, $T_{vj} = 25^{\circ}\text{C}$ $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 6,8\ \Omega$, $T_{vj} = 125^{\circ}\text{C}$	E_{on}		10,0		mJ mJ
Abschaltverlustenergie pro Puls turn-off energy loss per pulse	$I_C = 100\text{ A}$, $V_{CE} = 600\text{ V}$, $L_S = 60\text{ nH}$ $V_{GE} = \pm 15\text{ V}$, $R_{Goff} = 6,8\ \Omega$, $T_{vj} = 25^{\circ}\text{C}$ $V_{GE} = \pm 15\text{ V}$, $R_{Goff} = 6,8\ \Omega$, $T_{vj} = 125^{\circ}\text{C}$	E_{off}		12,0		mJ mJ
Kurzschlußverhalten SC data	$t_P \leq 10\ \mu\text{s}$, $V_{GE} \leq 15\text{ V}$ $T_{vj} \leq 125^{\circ}\text{C}$, $V_{CC} = 900\text{ V}$, $V_{CEmax} = V_{CES} - L_{sCE} \cdot di/dt$	I_{SC}		650		A
Innerer Wärmewiderstand thermal resistance, junction to case	pro IGBT per IGBT	R_{thJC}			0,16	K/W

Diode-Wechselrichter / diode-inverter**Höchstzulässige Werte / maximum rated values**

Periodische Spitzensperrspannung repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	1200	V
Dauergleichstrom DC forward current		I_F	100	A
Periodischer Spitzenstrom repetitive peak forward current	$t_P = 1\text{ ms}$	I_{FRM}	200	A
Grenzlastintegral I^2t - value	$V_R = 0\text{ V}$, $t_P = 10\text{ ms}$, $T_{vj} = 125^{\circ}\text{C}$	I^2t	1700	A^2s

Charakteristische Werte / characteristic values

			min.	typ.	max.	
Durchlassspannung forward voltage	$I_F = 100\text{ A}$, $V_{GE} = 0\text{ V}$, $T_{vj} = 25^{\circ}\text{C}$ $I_F = 100\text{ A}$, $V_{GE} = 0\text{ V}$, $T_{vj} = 125^{\circ}\text{C}$	V_F		1,80 1,70	2,30 2,20	V V
Rückstromspitze peak reverse recovery current	$I_F = 100\text{ A}$, $-di_F/dt = 2700\text{ A}/\mu\text{s}$ $V_R = 600\text{ V}$, $V_{GE} = -15\text{ V}$, $T_{vj} = 25^{\circ}\text{C}$ $V_R = 600\text{ V}$, $V_{GE} = -15\text{ V}$, $T_{vj} = 125^{\circ}\text{C}$	I_{RM}		125 155		A A
Sperrverzögerungsladung recovered charge	$I_F = 100\text{ A}$, $-di_F/dt = 2700\text{ A}/\mu\text{s}$ $V_R = 600\text{ V}$, $V_{GE} = -15\text{ V}$, $T_{vj} = 25^{\circ}\text{C}$ $V_R = 600\text{ V}$, $V_{GE} = -15\text{ V}$, $T_{vj} = 125^{\circ}\text{C}$	Q_r		12,0 22,0		μC μC
Abschaltenergie pro Puls reverse recovery energy	$I_F = 100\text{ A}$, $-di_F/dt = 2700\text{ A}/\mu\text{s}$ $V_R = 600\text{ V}$, $V_{GE} = -15\text{ V}$, $T_{vj} = 25^{\circ}\text{C}$ $V_R = 600\text{ V}$, $V_{GE} = -15\text{ V}$, $T_{vj} = 125^{\circ}\text{C}$	E_{rec}		4,00 9,00		mJ mJ
Innerer Wärmewiderstand thermal resistance, junction to case	pro Diode per diode	R_{thJC}			0,30	K/W

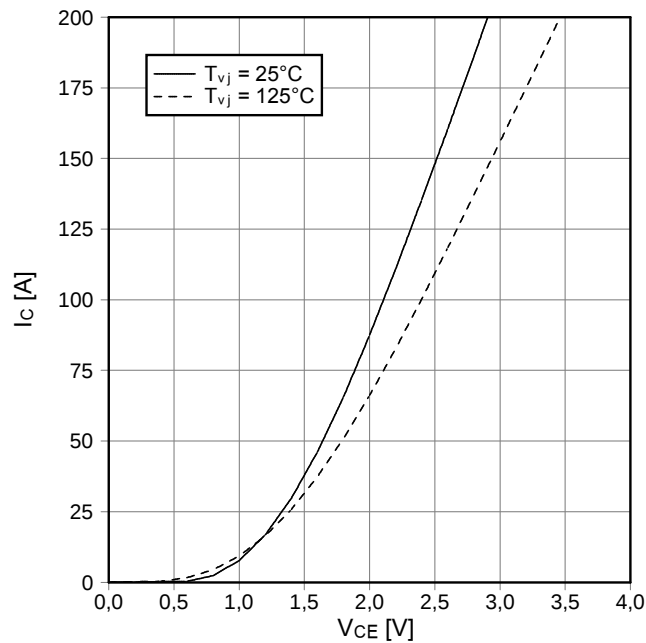
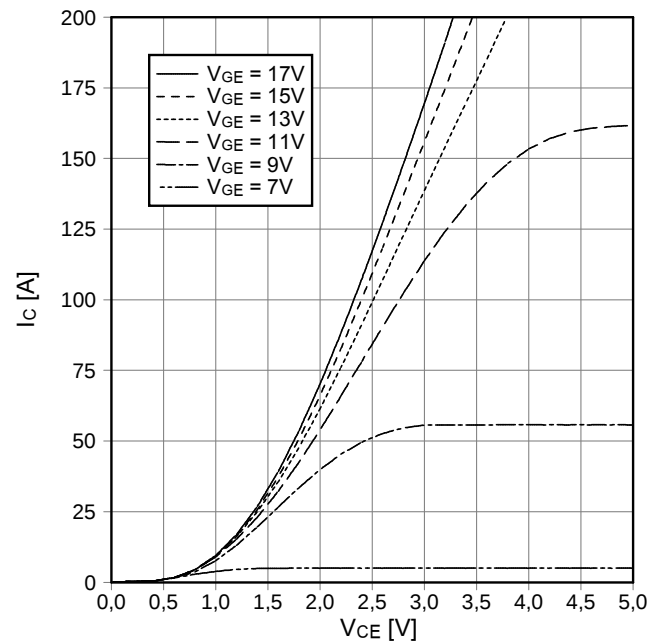
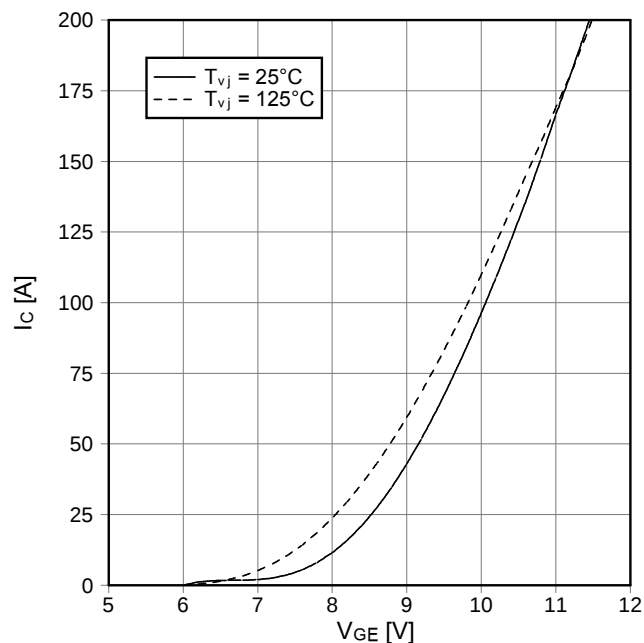
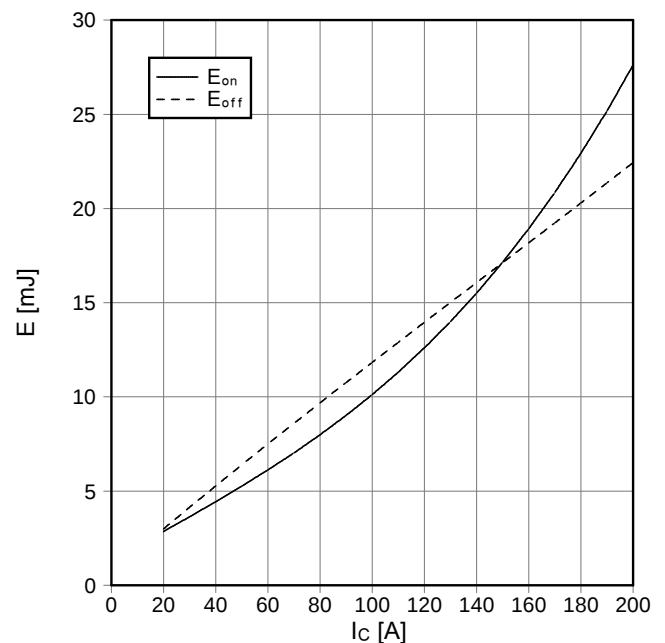
Modul / module

Isolations-Prüfspannung insulation test voltage	RMS, f = 50 Hz, t = 1 min.	V _{ISO}	2,5		kV
Material Modulgrundplatte material of module baseplate			Cu		
Material für innere Isolation material for internal insulation			Al ₂ O ₃		
Kriechstrecke creepage distance	Kontakt - Kühlkörper / terminal to heatsink Kontakt - Kontakt / terminal to terminal		20,0		mm
Luftstrecke clearance distance	Kontakt - Kühlkörper / terminal to heatsink Kontakt - Kontakt / terminal to terminal		11,0		mm
Vergleichszahl der Kriechwegbildung comparative tracking index		CTI	> 425		
		min. typ. max.			
Übergangs-Wärmewiderstand thermal resistance, case to heatsink	pro Modul / per module $\lambda_{\text{Paste}} = 1 \text{ W/(m}\cdot\text{K)} / \lambda_{\text{grease}} = 1 \text{ W/(m}\cdot\text{K)}$	R _{thCH}		0,01	K/W
Modulinduktivität stray inductance module		L _{sCE}		20	nH
Modulleitungswiderstand, Anschlüsse - Chip module lead resistance, terminals - chip	T _C = 25°C, pro Zweig / per arm	R _{CC'+EE'}		0,70	mΩ
Höchstzulässige Sperrschichttemperatur maximum junction temperature		T _{vj max}			150 °C
Temperatur im Schaltbetrieb temperature under switching conditions		T _{vj op}	-40		125 °C
Lagertemperatur storage temperature		T _{stg}	-40		125 °C
Anzugsdrehmoment f. mech. Befestigung mounting torque	Schraube / screw M6	M	3,00	-	6,00 Nm
Anzugsdrehmoment f. elektr. Anschlüsse terminal connection torque	Schraube / screw M6	M	2,5	-	5,0 Nm
Gewicht weight		G		340	g

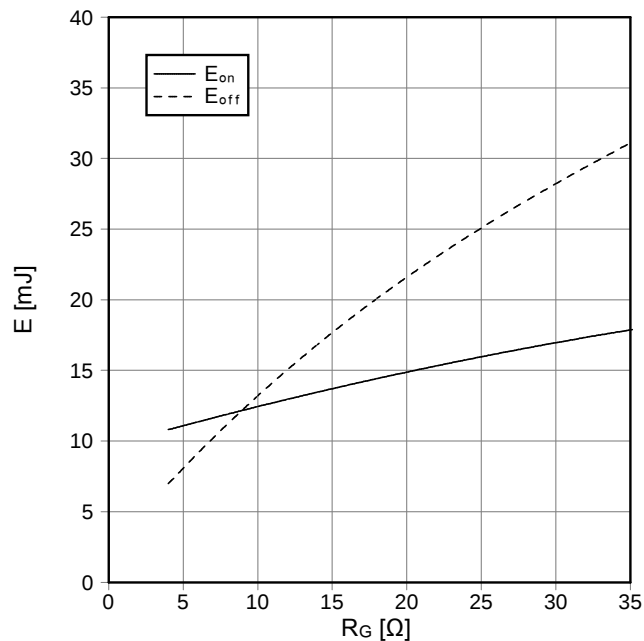
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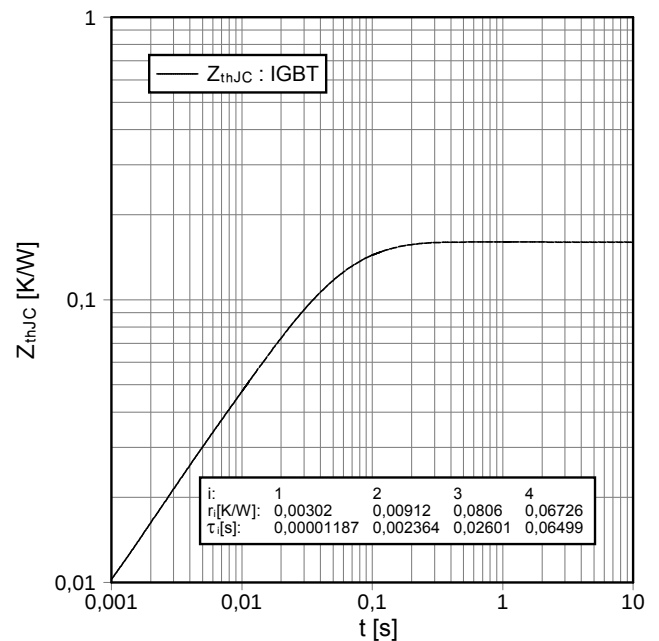
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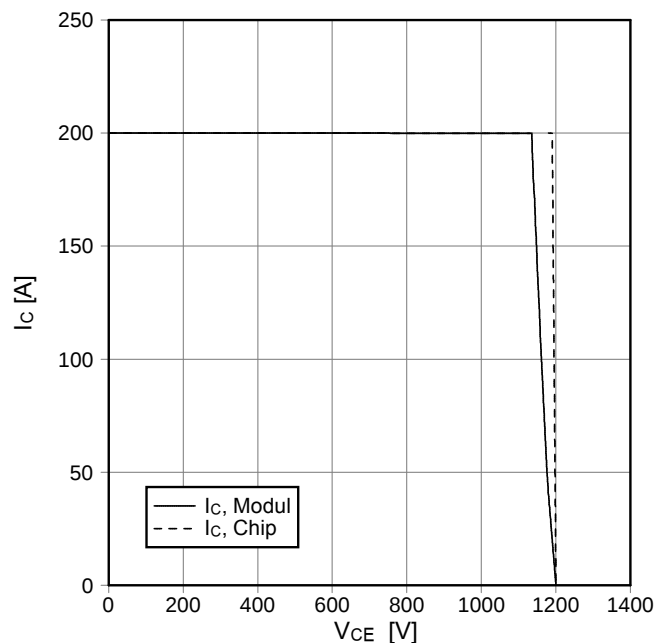
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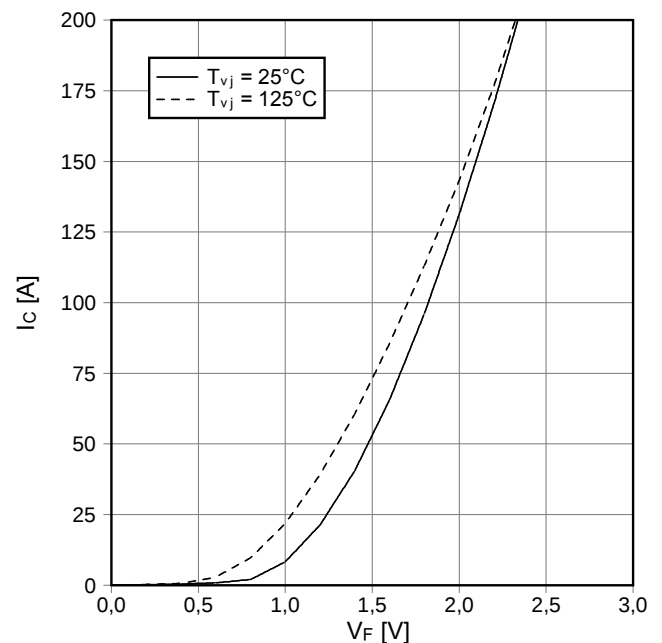
Ausgangskennlinie IGBT-Wechselr. (typisch)
output characteristic IGBT-inverter (typical) $I_C = f(V_{CE})$
 $V_{GE} = 15\text{ V}$ **Ausgangskennlinienfeld IGBT-Wechselr. (typisch)**
output characteristic IGBT-inverter (typical) $I_C = f(V_{CE})$
 $T_{vj} = 125^\circ\text{C}$ **Übertragungscharakteristik IGBT-Wechselr. (typisch)**
transfer characteristic IGBT-inverter (typical) $I_C = f(V_{GE})$
 $V_{CE} = 20\text{ V}$ **Schaltverluste IGBT-Wechselr. (typisch)**
switching losses IGBT-inverter (typical) $E_{on} = f(I_C)$, $E_{off} = f(I_C)$
 $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 6,8\ \Omega$, $R_{Goff} = 6,8\ \Omega$, $V_{CE} = 600\text{ V}$,
 $T_{vj} = 125^\circ\text{C}$ 

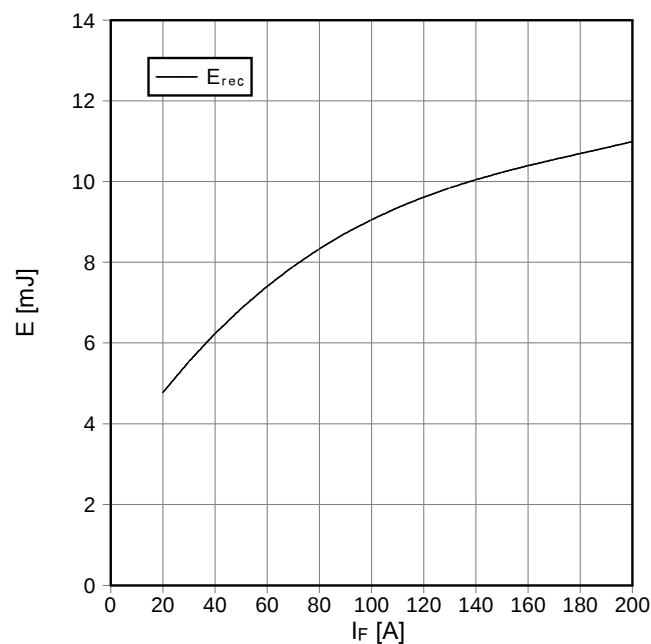
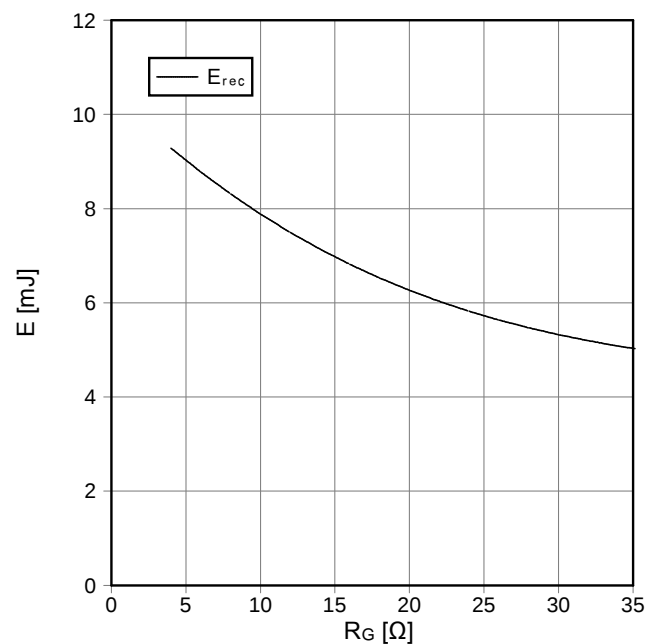
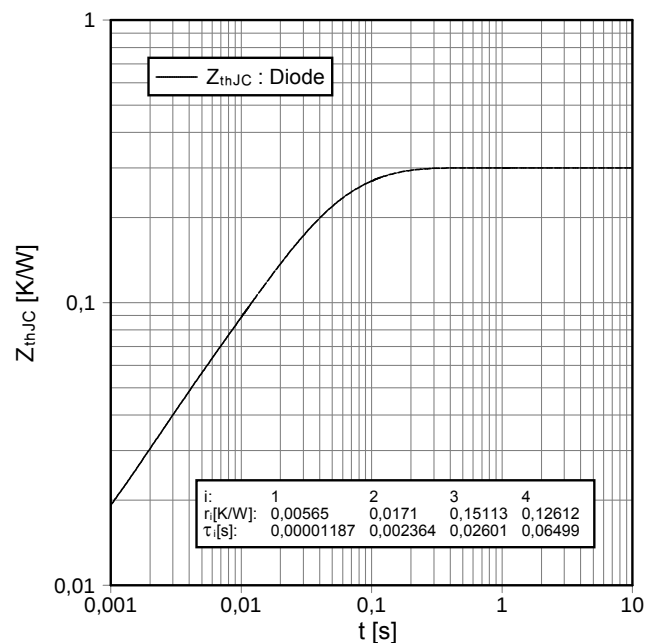
Schaltverluste IGBT-Wechselr. (typisch)
switching losses IGBT-Inverter (typical)

 $E_{on} = f(R_G)$, $E_{off} = f(R_G)$
 $V_{GE} = \pm 15 \text{ V}$, $I_C = 100 \text{ A}$, $V_{CE} = 600 \text{ V}$, $T_{vj} = 125^\circ\text{C}$

Transienter Wärmewiderstand IGBT-Wechselr.
transient thermal impedance IGBT-inverter

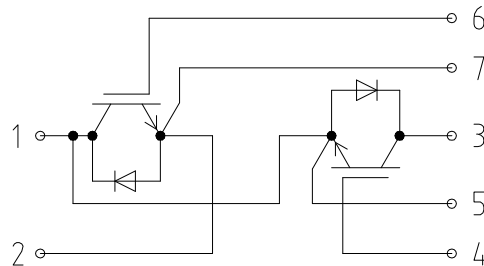
 $Z_{thJC} = f(t)$

Sicherer Rückwärts-Arbeitsbereich IGBT-Wr. (RBSOA)
reverse bias safe operating area IGBT-inv. (RBSOA)

 $I_C = f(V_{CE})$
 $V_{GE} = \pm 15 \text{ V}$, $R_{Goff} = 6,8 \Omega$, $T_{vj} = 125^\circ\text{C}$

Durchlaßkennlinie der Diode-Wechselr. (typisch)
forward characteristic of diode-inverter (typical)

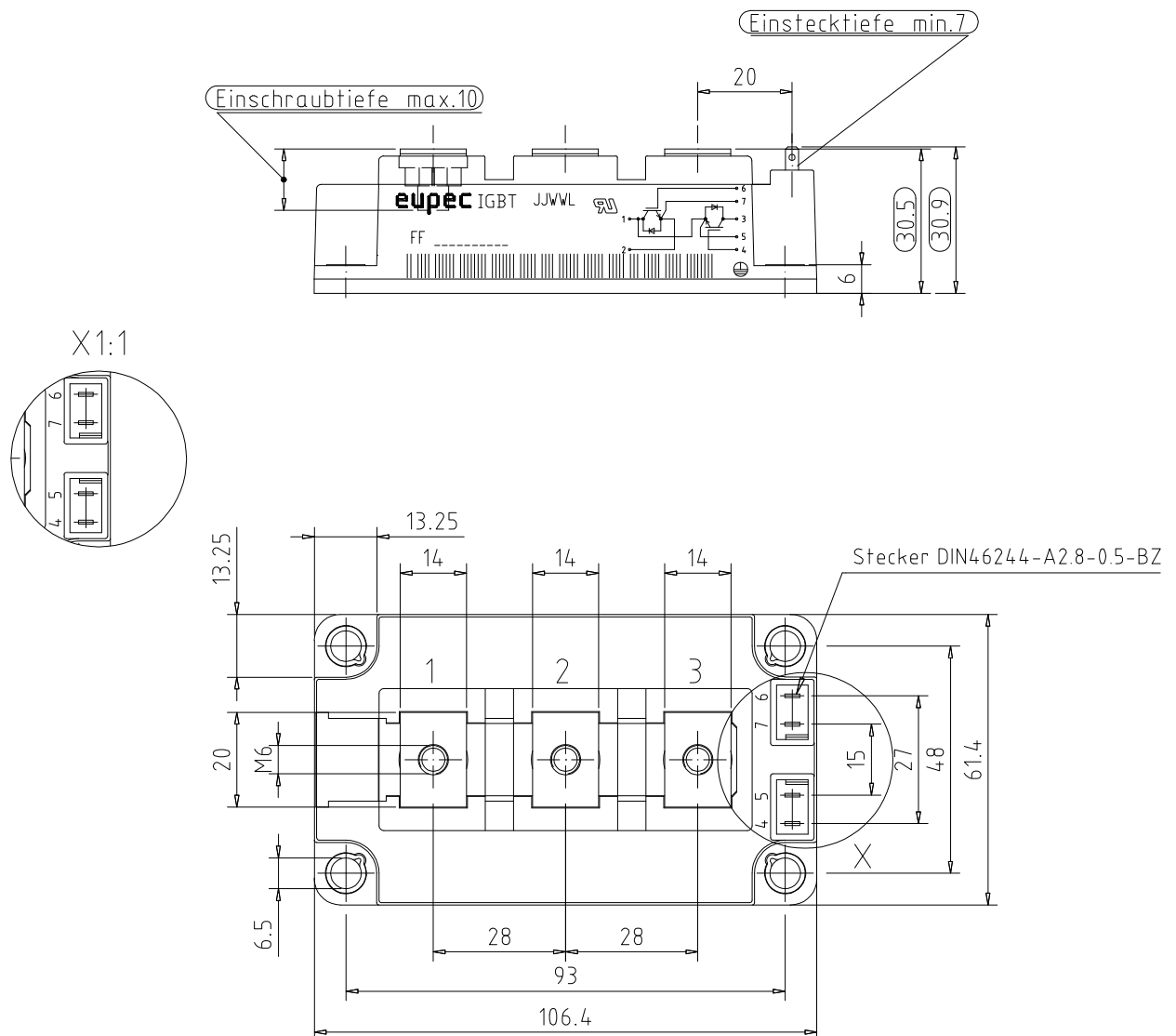
 $I_F = f(V_F)$


Schaltverluste Diode-Wechselr. (typisch)
switching losses diode-inverter (typical) $E_{rec} = f(I_F)$
 $R_{Gon} = 6,8 \Omega$, $V_{CE} = 600 \text{ V}$, $T_{vj} = 125^\circ\text{C}$ **Schaltverluste Diode-Wechselr. (typisch)**
switching losses diode-inverter (typical) $E_{rec} = f(R_G)$
 $I_F = 100 \text{ A}$, $V_{CE} = 600 \text{ V}$, $T_{vj} = 125^\circ\text{C}$ **Transienter Wärmewiderstand Diode-Wechselr.**
transient thermal impedance diode-inverter $Z_{thJC} = f(t)$ 

Schaltplan / circuit diagram



Gehäuseabmessungen / package outlines



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